Designs for a two-dimensional Si quantum dot array with spin qubit addressability

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Abstract

Electron spins in Si are an attractive platform for quantum computation, backed with their scalability and fast, high-fidelity quantum logic gates. Despite the importance of two-dimensional integration with efficient connectivity between qubits for medium- to large-scale quantum computation, however, a practical device design that guarantees qubit addressability is yet to be seen. Here, we propose a practical $3 \times$ 3 quantum dot device design and a larger-scale design as a longer-term target. The design goal is to realize qubit connectivity to the four nearest neighbors while ensuring addressability. We show that a 3×3 quantum dot array can execute four-qubit Grover's algorithm more efficiently than the one-dimensional counterpart. To scale up the two-dimensional array beyond 3×3 , we propose a novel structure with ferromagnetic gate electrodes. Our results showcase the possibility of medium-sized quantum processors in Si with fast quantum logic gates and long coherence times.

EDSR by micromagnets: requirements

Two requirements:

Stray field gradient •

Electric field •



EDSR by micromagnets: goals

Two goals:

• High driving field

• Single qubit addressability



1) Overcome addressability problem in two dimensional arrays

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Overcome addressability problem in 2x2 arrays



Old design

Yoneda et al., Appl. Phys. Express 8, 084401 (2015)





Device setup

- ²⁸Si/SiGe heterostructure
- Spin readout via gatebased sensing
- Initialization via relaxation and adiabatic passage
- Manipulation: EDSR

Table 1. Overlapping-layer gate characteristics.							
Layer index	Gate name	Gate color	Gate width (nm)	Gate height (nm)			
1	$\begin{array}{c} B_{11\text{-}12},B_{12\text{-}13}\\ B_{r1\text{-}11},B_{r2\text{-}13}\end{array}$	Blue	50	15			
2	P_{11}, P_{12}	Red	90	25			
3	$B_{12 \cdot 22}, B_{21 \cdot 22}$	Yellow	60	40			
4	P_{22}	Magenta	70	60			



Performance

- f_{Rabi} = 6.8 14 MHz, assuming wavefunction displacement of 0.43 nm
- Minimum $\Delta B = 6$ mT, which corresponds to $\Delta f = 160$ MHz

- Qubit 143 nm below the magnets
- External field: NA, assumed fully magnetized magnets
- Displacement: along y



Linear vs 2D array performance

Implementation of a4qubit Grover's search algorithm

- 2d: 15 two-qubit gates (2 SWAP)
- Linear: 18 two-qubit gates (5 SWAP)



1) Overcome addressability problem in two dimensional arrays

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Find a scalable path towards thousands of qubits

a 1.5 µm 0.9 µm 1.7 µm 0.2 µm 0.425 µm ++ 0.1 µm 0.15 µm 0.6 µm 0.15 um 0.425 µm 1.7 µm B_{ext} b_{trans} (mT/nm) $B_{\rm long}$ (mT) b С 1.5 200 1 100 0 0.5 -100 0 -200 -0.5 -300 -1 -400 -1.5 -500

Old design

New idea

Separate the magnet:

- General magnet for addressability
- One magnet for each qubit for high driving gradient

Solution: ferromagnetic gates

- Plunger and barrier gates are magnetic
- Created as vias
- Size QD=120x120 nm²





Barrier gate Data qubits Ancilla qubits

Performance

- f_{Rabi} = 39 MHz, assuming wavefunction displacement of 0.43 nm
- Δf > 100 MHz
- QD footprint: 120x120 nm²

- Qubit position: NA
- External field: NA, assumed fully magnetized magnets
- Displacement: along y





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Issues

- Vias fan-out and connection
- Magnetization pattern uniformity







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Comparison: global magnetic field

- Deliver of magnetic field trough MW dielectric resonator
- Brought in resonance by local voltage (g-factor modulation)
- Demonstrated coherent Rabi oscillation





Kane, B. E. Nature 393, 133– 137 (1998).

Vahapoglu, E., et al., Science Advances, 7(33), (2021)



Vahapoglu, E., et al., arXiv:2107.14622 (2021) Issues

- f_{Rabi} = < 2 MHz (saturation with increasing MW power)
- Unwanted additional drive
- Low quality factor for the resonator



Vahapoglu, E., et al., arXiv:2107.14622 (2021)

Comparison



Tadokoro et al. (arXiv:2106.11124)

- f_{Rabi} = 39 MHz
- Addressability via magnetic gradient
- Simulation



Vahapoglu et al. (arXiv:2107.1462)

- f_{Rabi} = 1.5 MHz
- Addressability tunable by voltage
- Experiment

Conclusion

 Proposal for EDSR drive up to thousand qubits

 Based on splitting magnet role between driving and addressability



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